

(19) World Intellectual Property Organization
International Bureau



(43) International Publication Date
28 August 2003 (28.08.2003)

PCT

(10) International Publication Number
WO 03/071549 A1

(51) International Patent Classification⁷: **G11C 11/34**,
H01L 45/00

(21) International Application Number: PCT/US03/03674

(22) International Filing Date: 10 February 2003 (10.02.2003)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
10/076,486 19 February 2002 (19.02.2002) US

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(81) Designated States (*national*): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, OM, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, TJ, TM, TN, TR, TT, TZ, UA, UG, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) Designated States (*regional*): ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

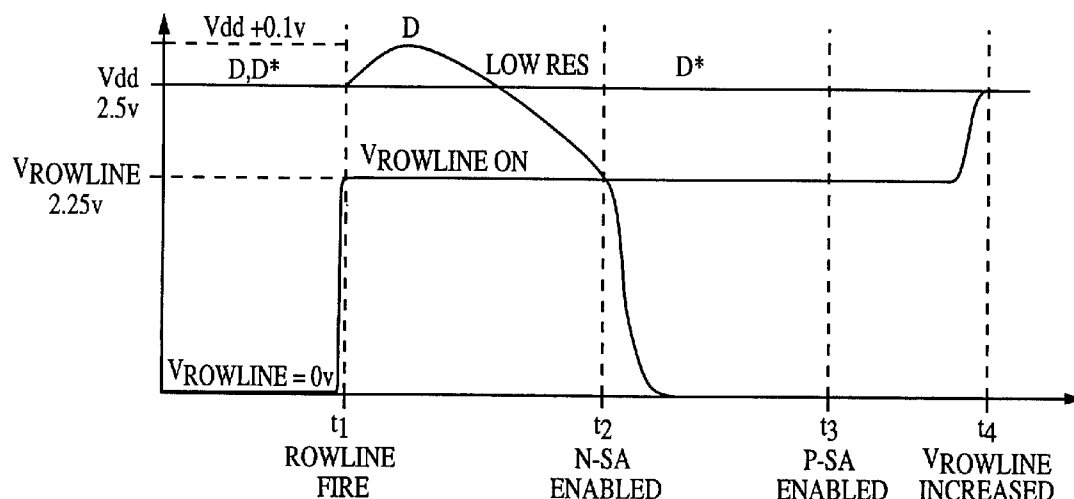
- with international search report
- before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments

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For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: PROGRAMMABLE CONDUCTOR RANDOM ACCESS MEMORY AND METHOD FOR SENSING SAME



(57) **Abstract:** A sense circuit for reading a resistance level of a programmable conductor random access memory (PCRAM) cell is provided. A voltage potential difference is introduced across a PCRAM cell by activating an access transistor from a raised rowline voltage. Both a digit line and a digit complement reference line are precharged to a first predetermined voltage. The cell being sensed has the precharged voltage discharged through the resistance of the programmable conductor memory element of the PCRAM cell. A comparison is made of the voltage read at the digit line and at the reference conductor. If the voltage at the digit line is greater than the reference voltage, the cell is read as a high resistance value (e.g., logic HIGH); however, if the voltage measured at the digit line is lower than that of the reference voltage, the cell is read as a low resistance value (e.g., logic LOW).